

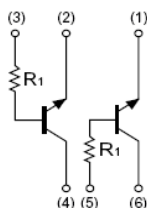
dual digital transistors (NPN+NPN)

FEATURES

Two DTC144T chips in a package.

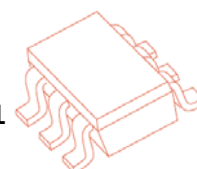
Marking: H14

Equivalent circuit



SOT-363

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Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-base Voltage	50	V
V_{CEO}	Collector-emitter Voltage	50	V
V_{EBO}	Emitter-base Voltage	5	V
I_C	Collector current	100	mA
P_D	Power dissipation	150	mW
T_J	Junction temperature	150	°C
T_{stg}	Storage temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$			500	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			500	nA
DC current transfer ration	h_{FE}	$V_{CE}=5V, I_C=1mA$	100		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=5mA, I_B=0.5mA$			0.3	V
Transition frequency	f_T	$V_{CE}=10V, I_C=5mA, f=100MHz$		250		MHz
Input resistance	R_1		32.9		61.1	KΩ